



SOT-523 Plastic-Encapsulate Diodes

BAS16T/BAW56T/BAV70T/BAV99T

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 150 mW ($T_{amb}=25^{\circ}C$)

Forward Current

I_F : 75 mA

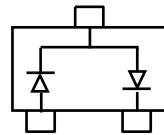
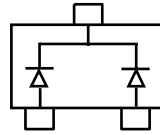
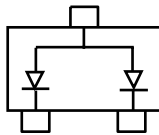
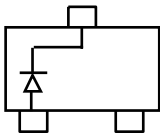
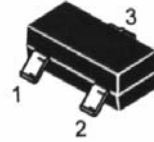
Reverse Voltage

V_R : 85 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-523



BAS16T Marking: A2

BAW56T Marking: JD

BAV70T Marking: JJ

BAV99T Marking: JE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R=75V$		2	μA
	I_{R2}	$V_R=25V$		0.03	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		1.5	pF
Reverse recovery time	t_{rr}			4	nS

Typical Characteristics

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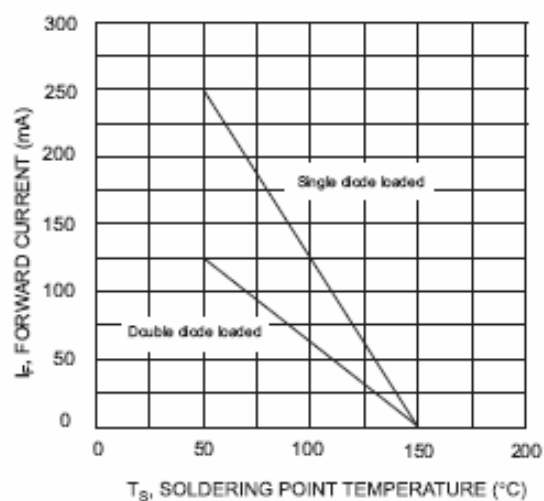


Fig. 1 Current Derating Curve

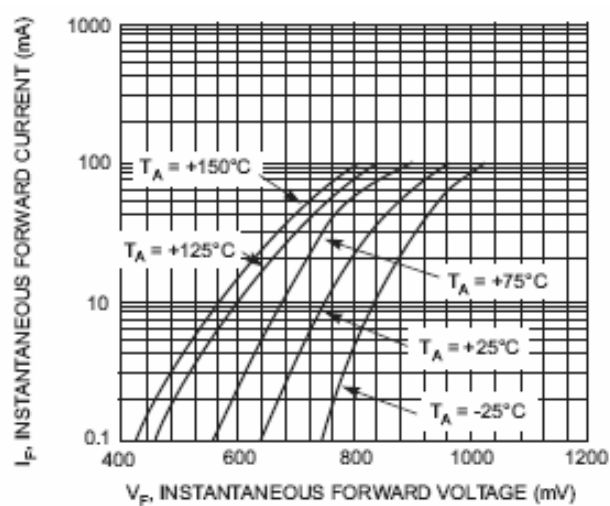


Fig. 2 Typical Forward Characteristics

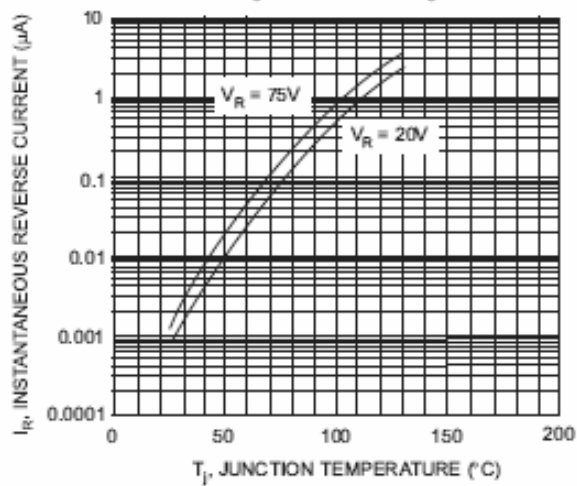


Fig. 3 Typical Reverse Characteristics